

## Supporting Information

# Fluoride Superionic Conduction in TlF with the New Anti- $\alpha$ -CuBr Structure Containing Intrinsic F Vacancies

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## Computational Methods; MD data to conductivity

Mean square displacements (MSDs) shown in Fig. 4(a) were calculated as

$$\text{MSD}(t) = \frac{1}{N} \sum_{i=1}^N |\mathbf{r}_i(t) - \mathbf{r}_i(0)|^2 \quad (1)$$

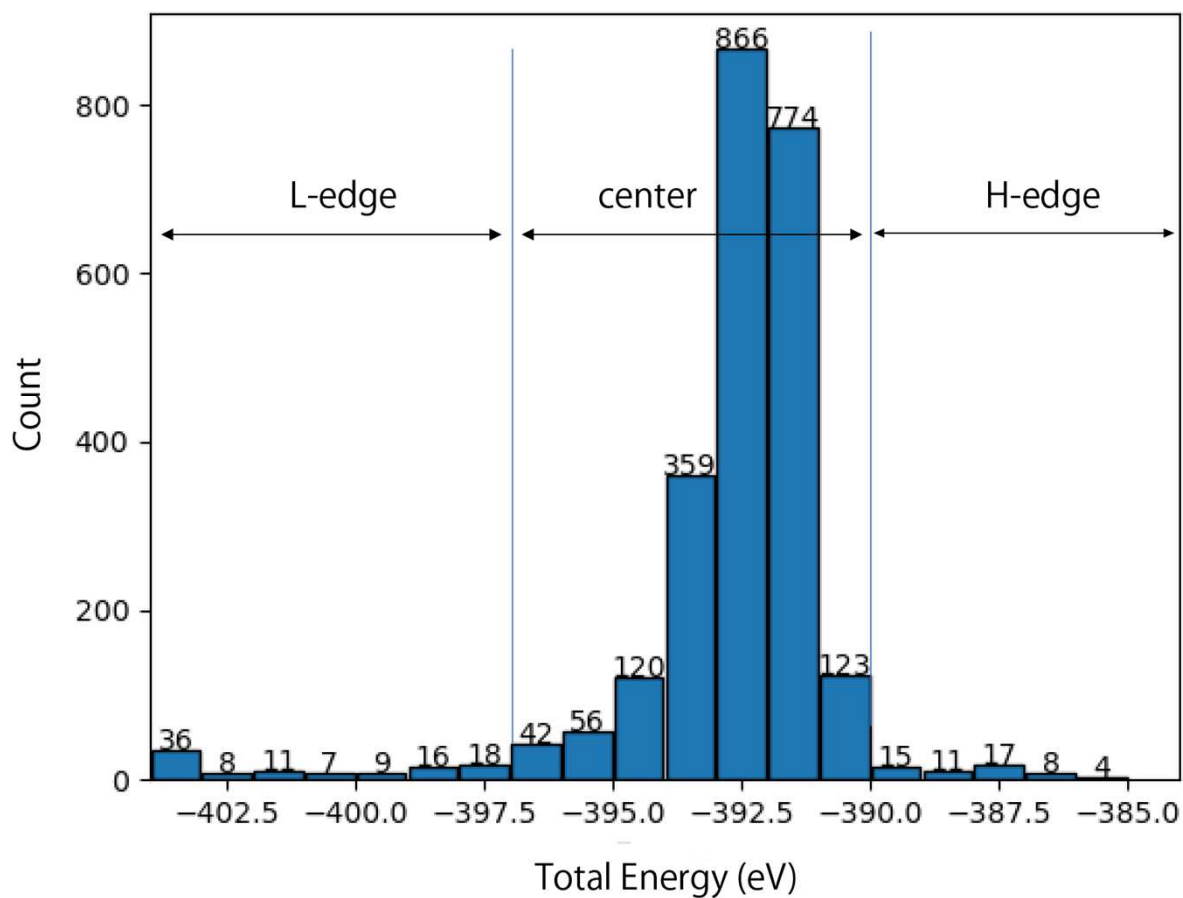
where  $\mathbf{r}_i(t)$  is the position vector of the  $i$ -th mobile ion at time  $t$ , and  $N$  is the total number of the mobile ions. To calculate diffusion coefficient  $D$ , we adopted the time-averaging form [1] as

$$D(\Delta t) = \frac{1}{6N\Delta t} \sum_{i=1}^N \langle |\mathbf{r}_i(t + \Delta t) - \mathbf{r}_i(t)|^2 \rangle_t \quad (2)$$

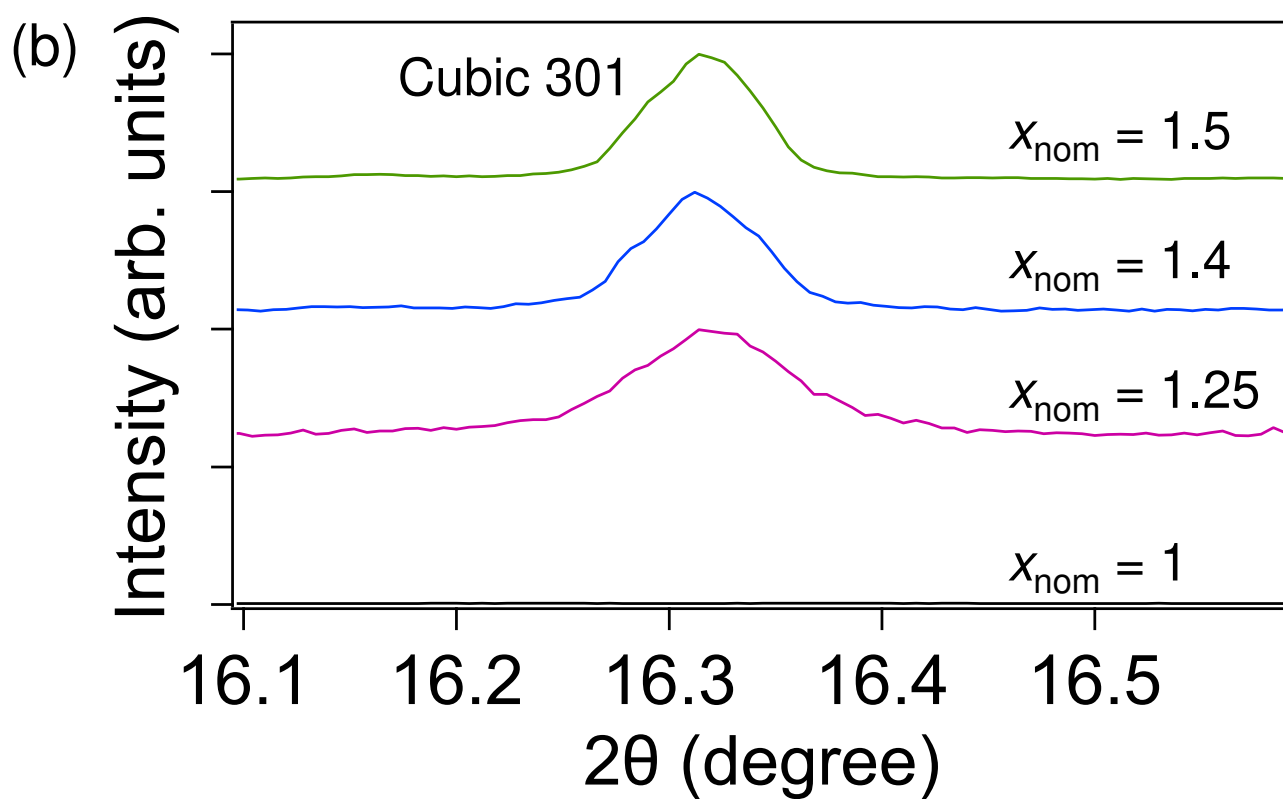
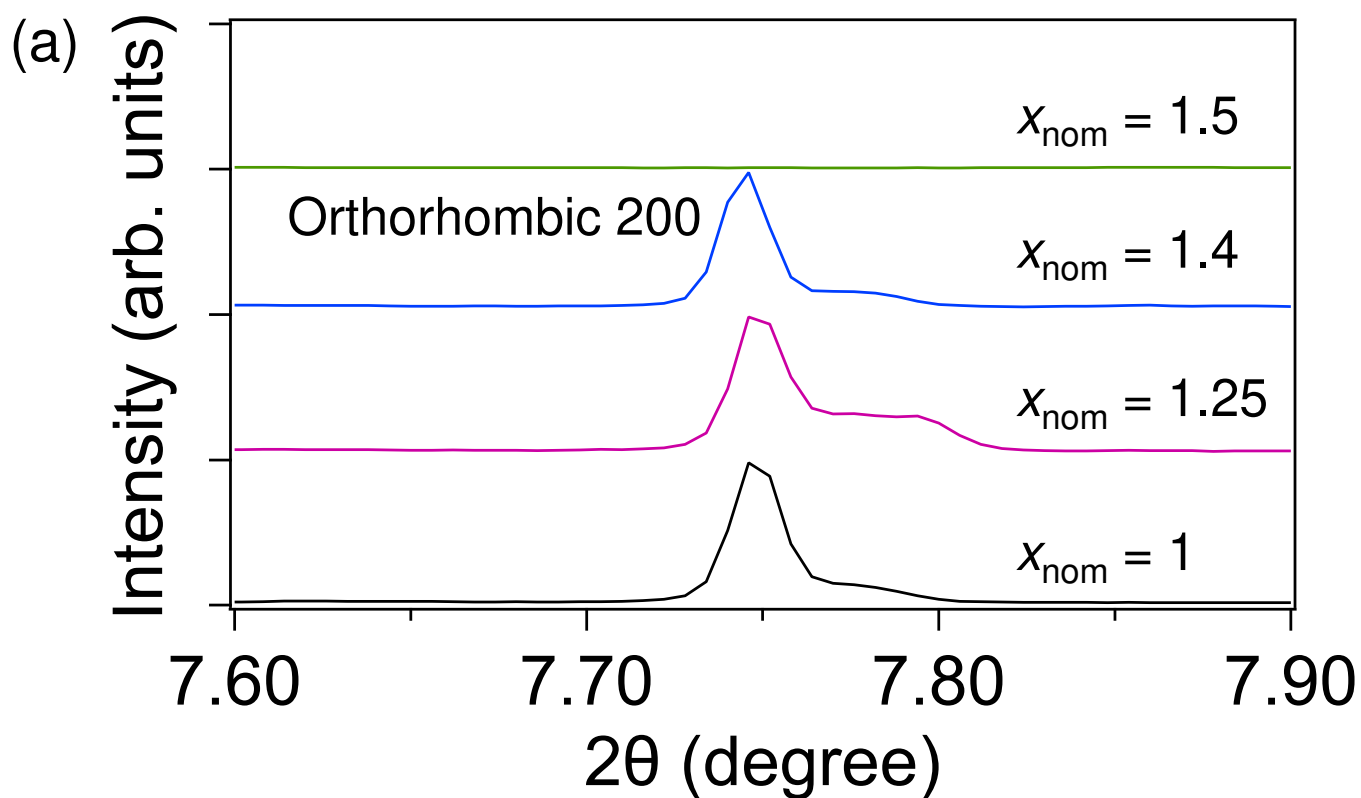
where the bracket represents averaging over  $t$ , which is intended for a good statistics. We calculate  $D(\Delta t)$  in terms of  $\Delta t$  and obtain a well converged  $D$  that is almost insensitive to  $\Delta t$  as shown in Fig. 4(b). The ionic conductivity,  $\sigma$ , can be calculated using Nernst-Einstein relationship as

$$\sigma = \frac{nq^2}{k_B T} D \quad (3)$$

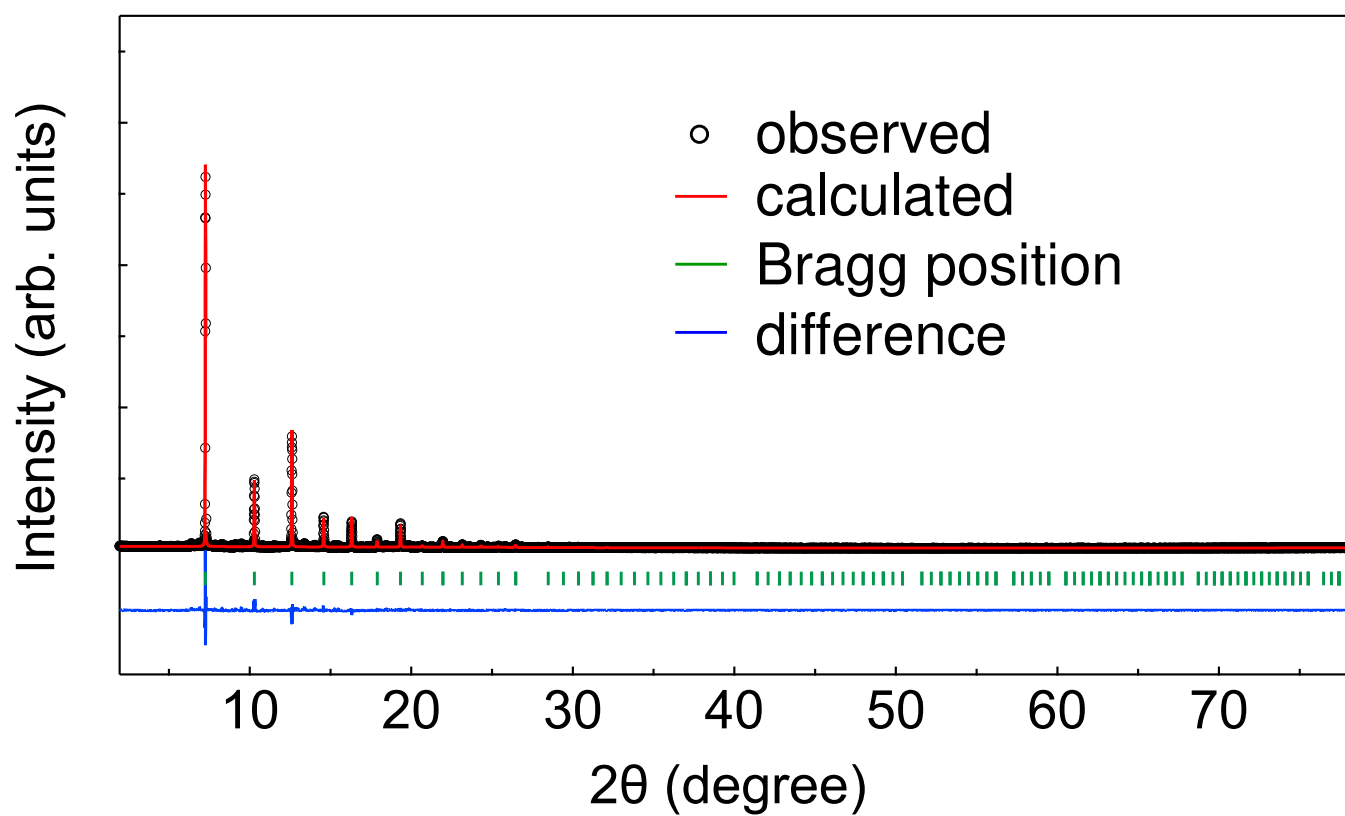
where  $n$  is the number of mobile ions per MD cell and  $q$  is the ionic charge.



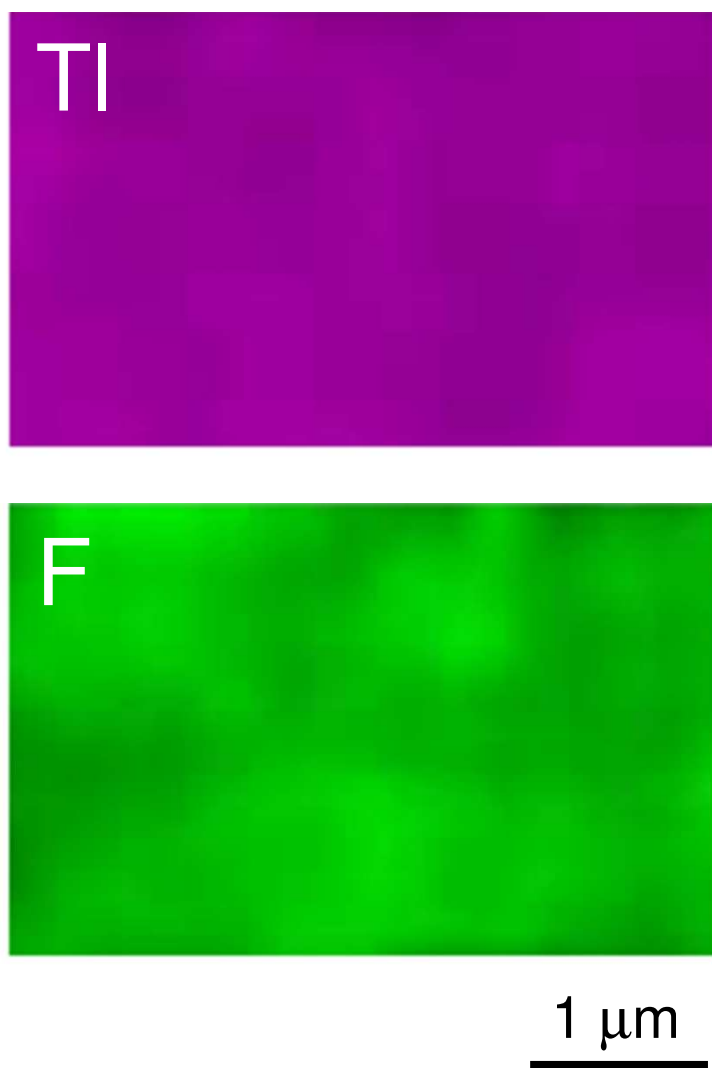
**Figure S1.** Example of the total energy histogram of an MD trajectory divided into three regions as left-edge, center, and right-edge. The left- and right-edges correspond to rare structures and the center major structures.



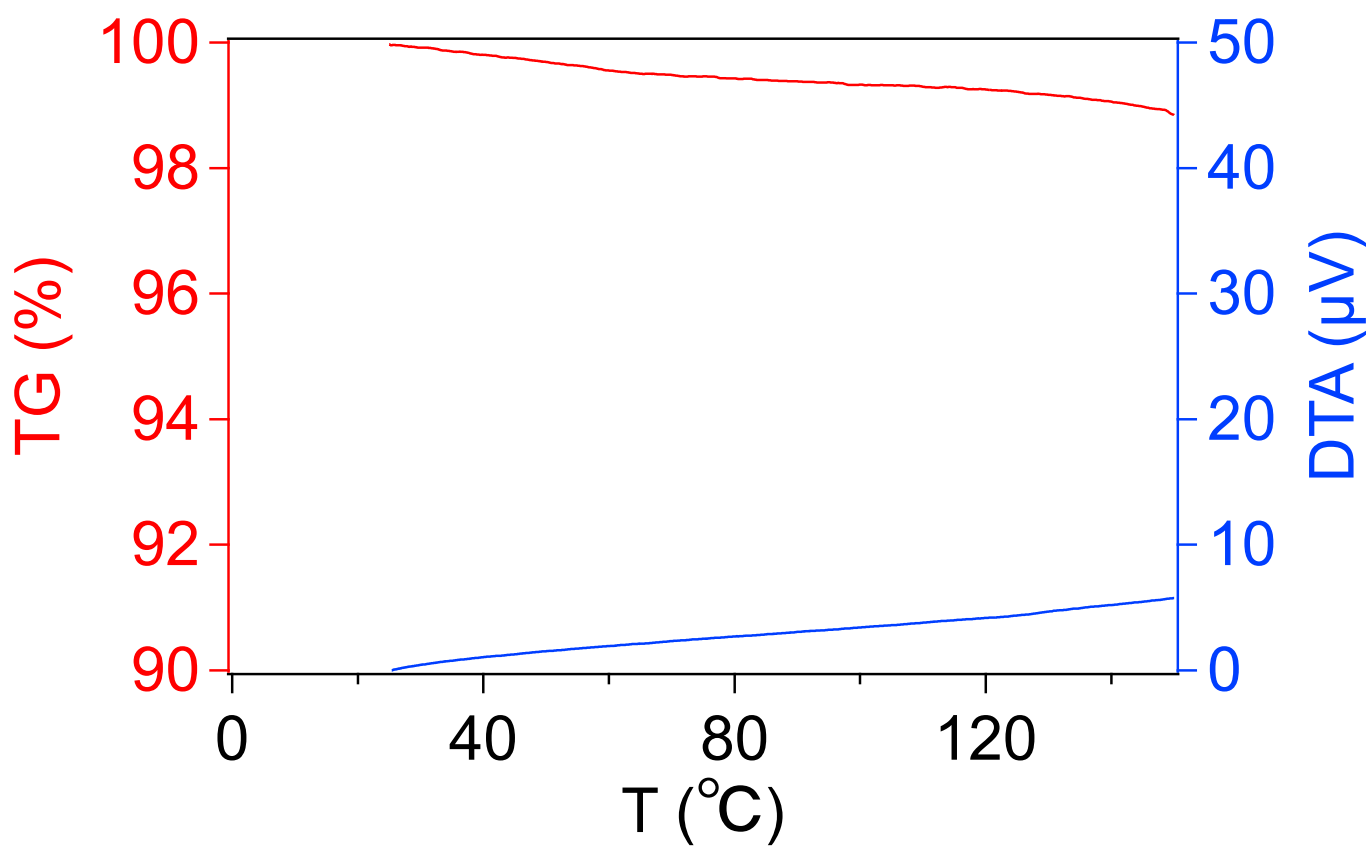
**Figure S2.** XRD patterns for (a) 200 peak for orthorhombic TiF and (b) 301 peak for cubic TiF.



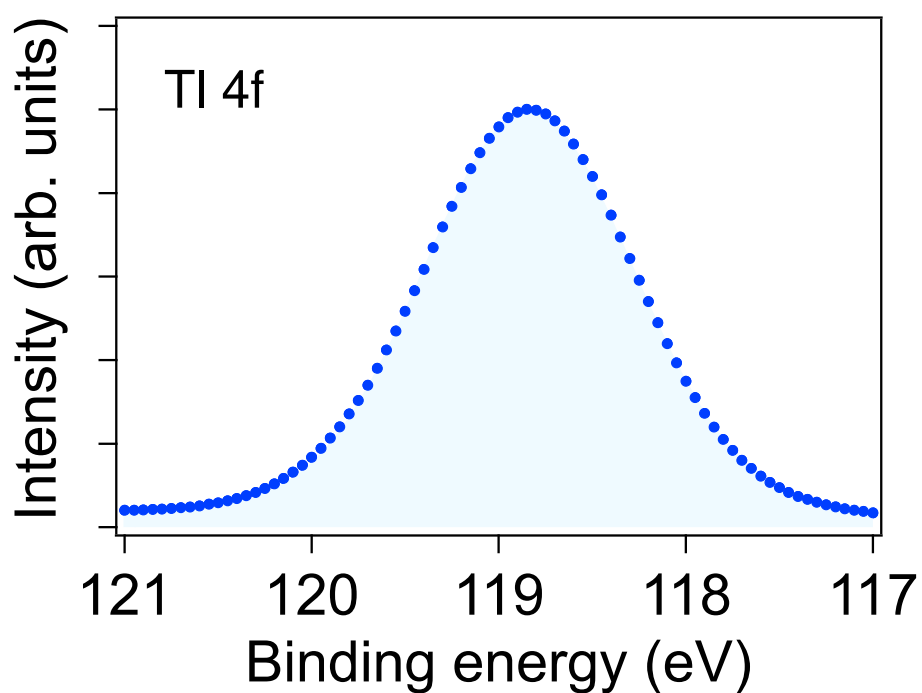
**Figure S3.** Rietveld refinement on synchrotron XRD pattern of cubic TlF.



**Figure S4.** SEM-EDX mapping images of cubic TlF. Scale bar: 1 μm.

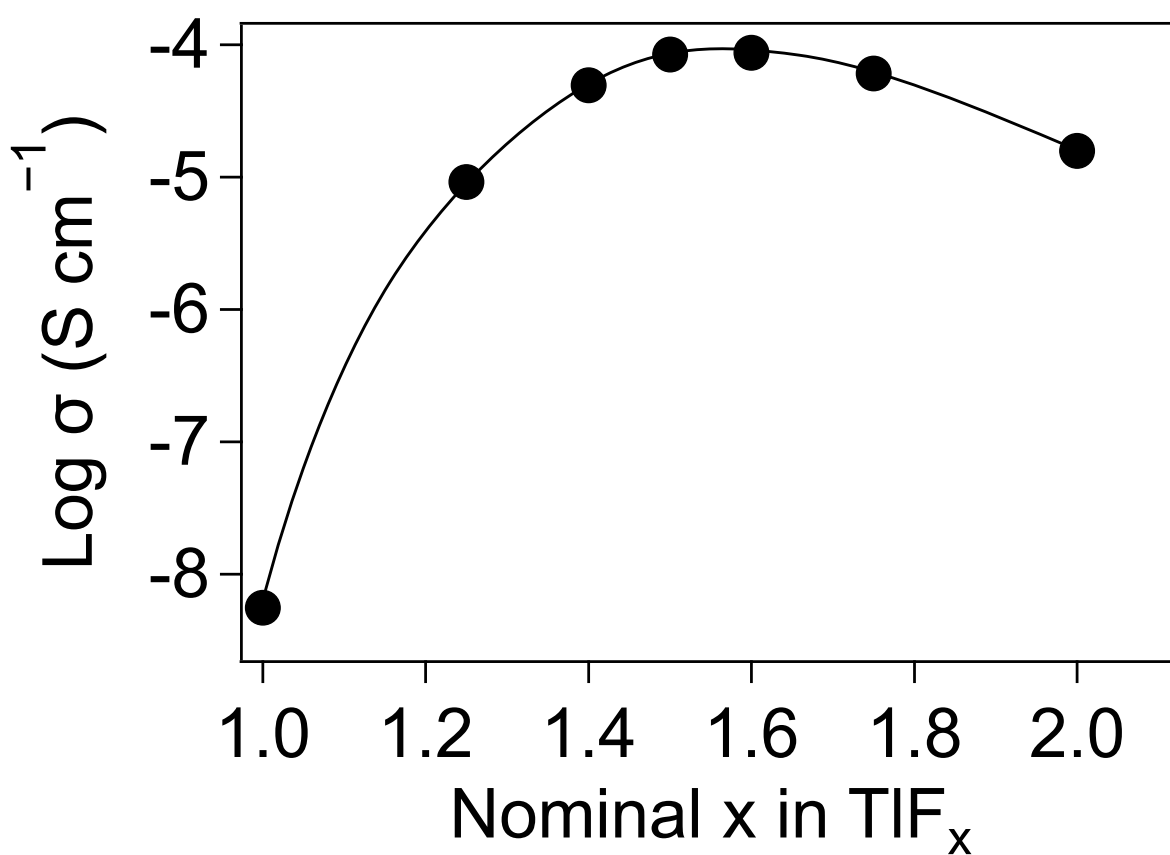


**Figure S5.** TG-DTA curves for cubic TlF.

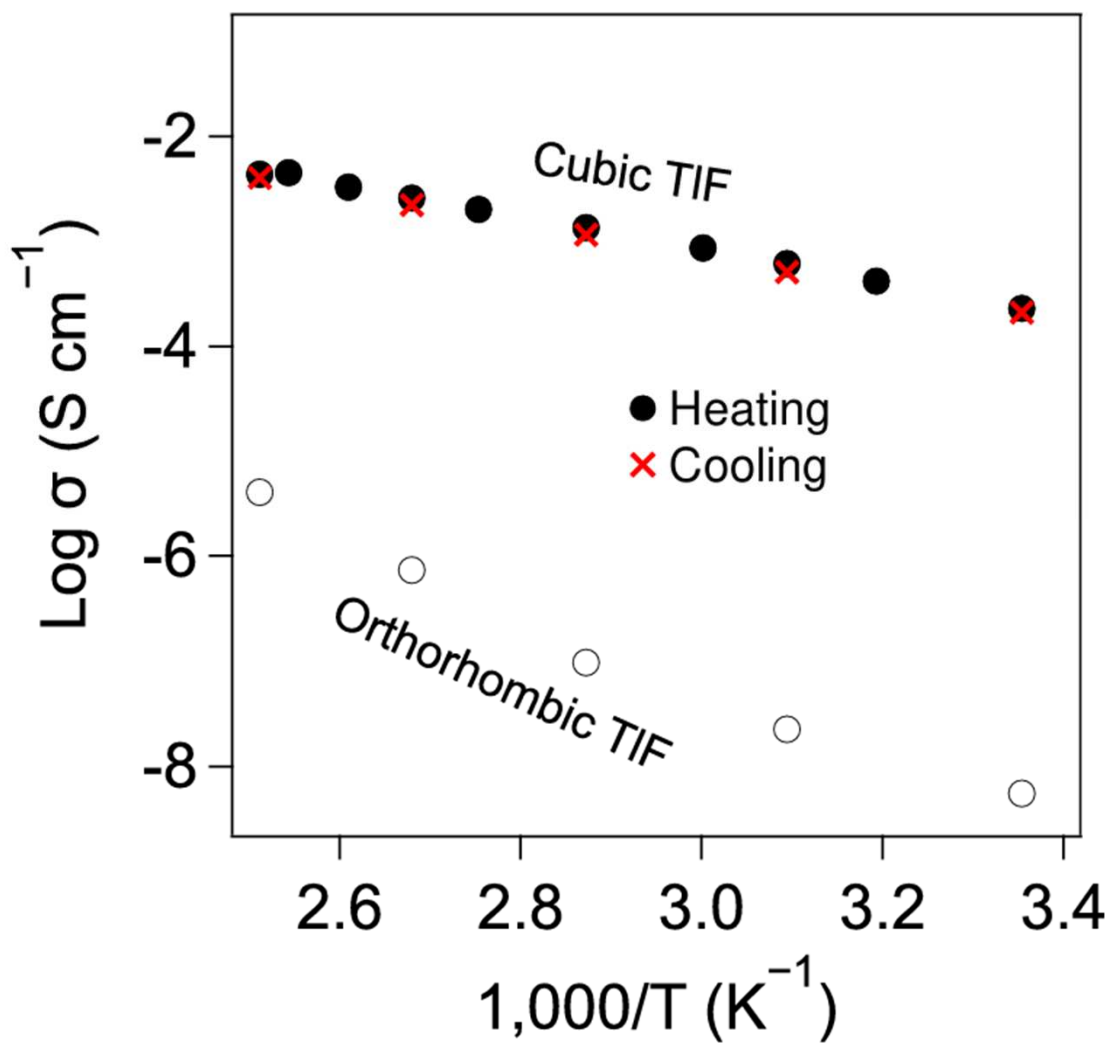


**Figure S6.** Tl 4f<sub>7/2</sub> XPS spectrum at room temperature for cubic TlF. The symbols and filled area show the experimental data and the fitted results, respectively.

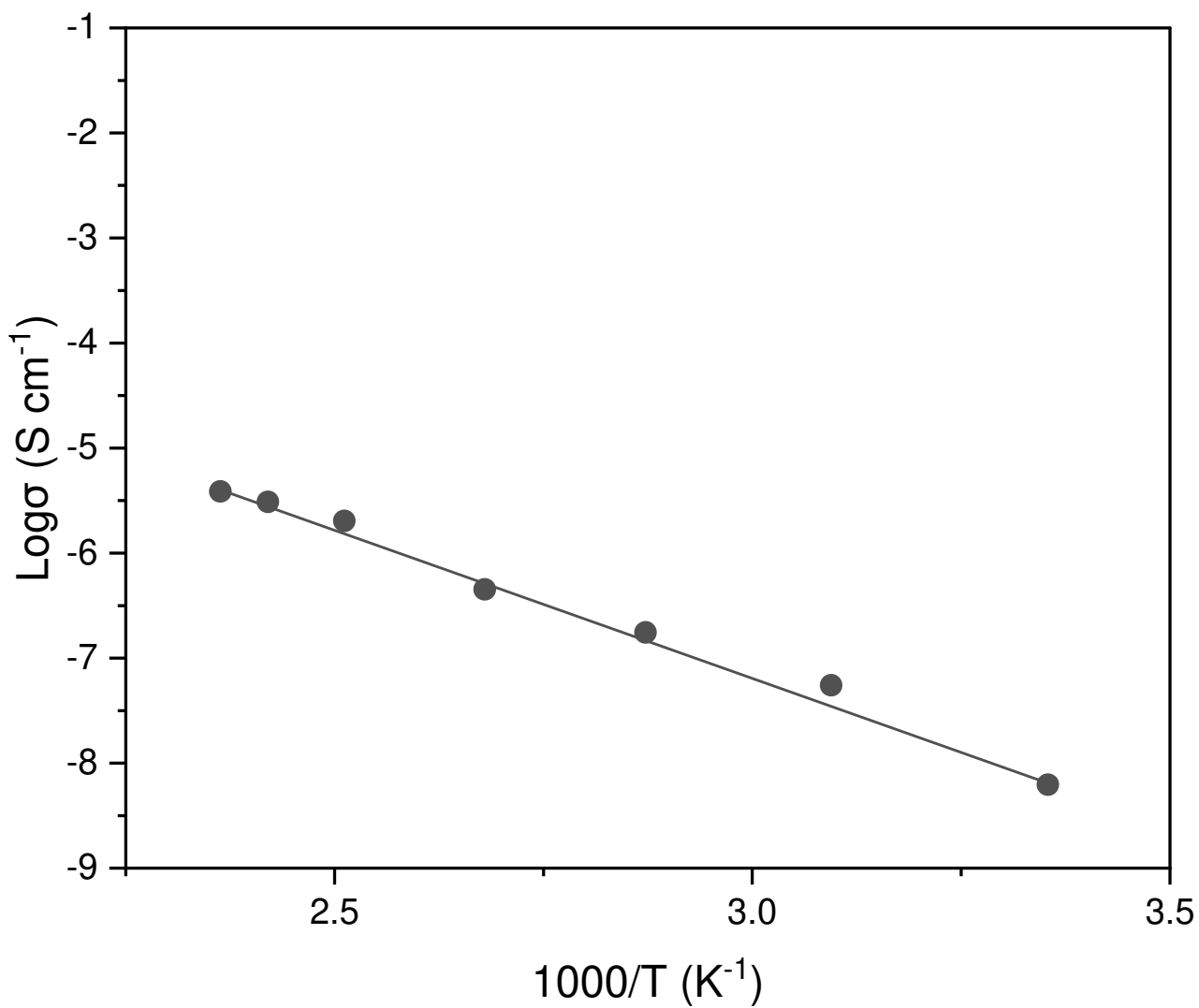




**Figure S7.** Room-temperature electrical conductivity as a function of nominal  $x$  of  $\text{TlF}_x$ . The solid line is the guide to the eyes.



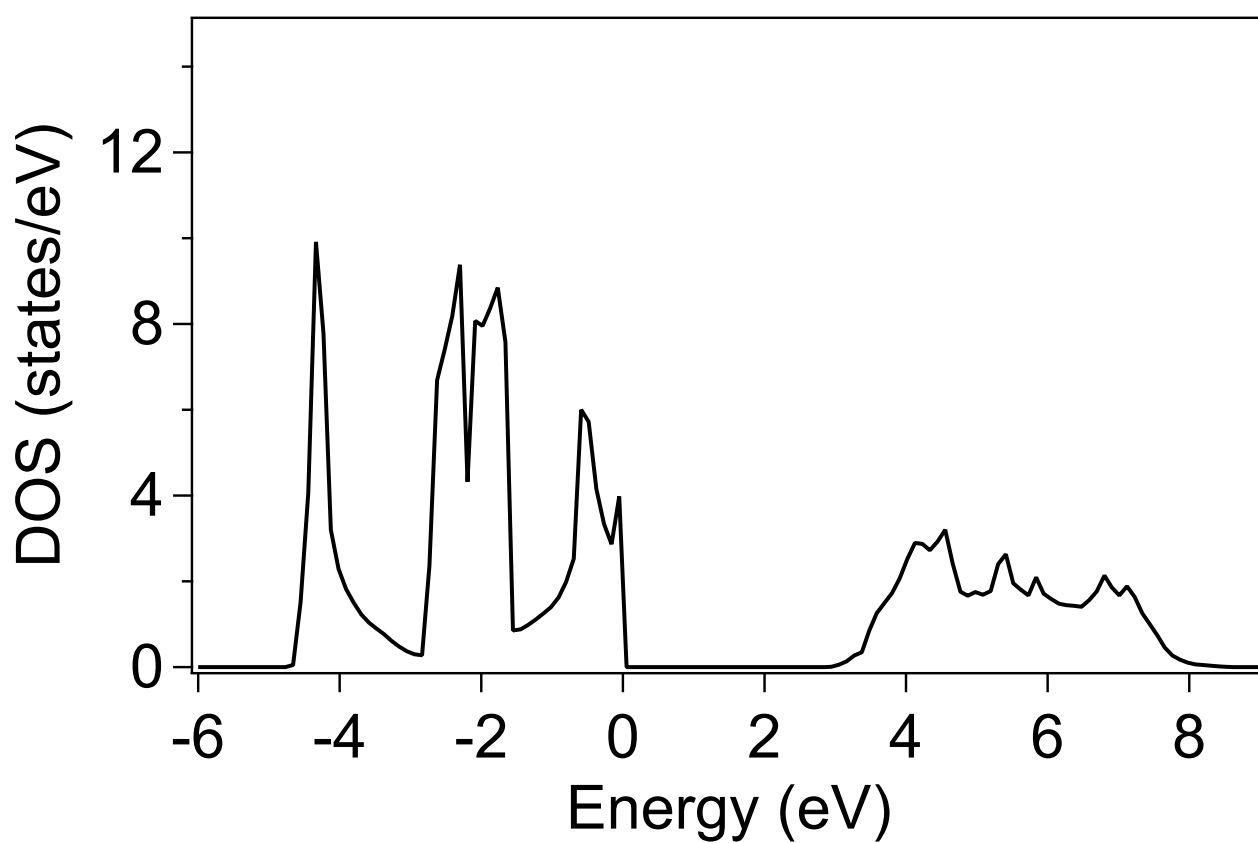
**Figure S8.** Fluoride-ion conductivity of cubic TlF upon heating and cooling, and orthorhombic TlF upon heating.



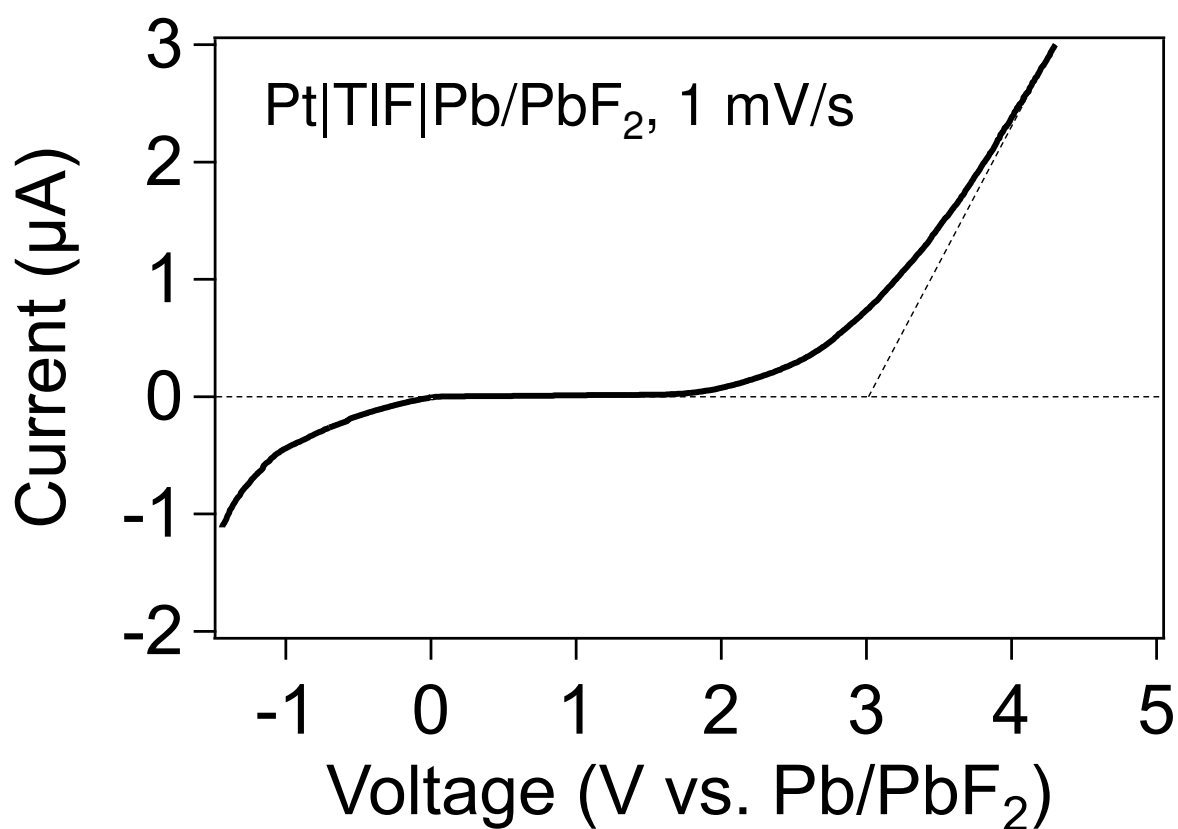
**Figure S9.** Arrhenius plot of the electronic conductivity for cubic TlF.



**Figure S10.** Photograph of the cubic TlF powder after the chemical fluorination using  $\text{XeF}_2$ .



**Figure S11.** Electronic density of states of cubic TlF. The Fermi level corresponds to 0 eV.



**Figure S12.** Electrochemical stability window of cubic TlF. The estimated stability limit is approximately 3.0 V at room temperature.

**Table S1.** Refined crystal parameters, space group, lattice parameters, reliability factors and agreement factor for cubic TlF at room temperature.  $g$ , occupancy;  $B$ , atomic displacement parameter. Here, the reliability factors  $R_{\text{WP}}$  and  $R_{\text{I}}$  are the weighted profile and integrated intensities, respectively.

Atom	Site	$g$	$x$	$y$	$z$	$B$ ( $\text{\AA}^2$ )
Tl	$2a$	1	0	0	0	0.322
F	$12d$	0.167(1)	1/4	0	1/2	5.195

Unit cell: Cubic  $Im\bar{3}m$ ,  
 $a = b = c = 4.6024(3)$   $\text{\AA}$ ,  
 $R_{\text{WP}} = 5.75\%$ ,  $R_{\text{I}} = 3.94\%$ ,  $S = 1.46$ .

## References

- [1] X. He, Y. Zhu, Y. Mo. *Nat. Commun.* 2017, **8**, 15893.